# TEST SYSTEMS

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#### Setting the Test Standard for Tomorrow

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### **Forward Looking Statements**

This presentation contains forward-looking statements that involve risks and uncertainties relating to projections regarding industry growth and customer demand for the Company's products. Actual results may vary from projected results. These risks and uncertainties include without limitation, acceptance by new customers of the FOX<sup>TM</sup> wafer level burn-in and test system, world economic conditions, the timing of COVID-19 related business impacts, the Company's ability to maintain sufficient cash to support operations, and the potential emergence of alternative technologies, which could adversely affect demand for the Company's products in fiscal year 2023. See the Company's recent 10-K and 10-Q reports filed with the SEC for a more detailed description of the risks facing the Company's business. The Company disclaims any obligation to update information contained in any forward-looking statement to reflect events or circumstances occurring after the date of this presentation.



### Aehr Test Systems Company Overview

#### **Production Semiconductor Test & Burn-in for over 40 Years!**

 Technology leader in massively parallel test and burn-in systems

- World-wide leader in waferlevel burn-in and test systems







 Unique full-wafer test and burnin systems and contactors

# **Testing without Compromise**

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#### Reliability, Stress, and DFT Testing without compromise

- Solutions for package parts, modules, panels, or wafers allow testing at optimal process point
- Confirm which devices received desired test with per device measurements, monitoring, & feedback
- 100% traceability with die location (wafer) or device ID read back (module) and electronic tracking ensures knowledge of "good" devices
- Thermal range, uniformity, and capacity permit reduced test times & confidence in target test conditions
- Vast system resources allow for minimal sharing (higher sample size, higher yields, fewer hostage failures)
- Economical solutions and customizations allow required testing to be performed at the lowest cost



#### **Worldwide Customer Base**



(Partial Customer List)



### **Market Drivers**

Need for cost-efficient wafer level and singulated die burn-in & testing as well as new requirements in package part burn-in are creating significant revenue opportunities in the following key markets

- Automotive IC growth in motor control and charging infrastructure using Silicon Carbide devices, as well as sensors, safety, information, and entertainment
- Data Center Infrastructure and unstoppable growth in Data Storage
- Worldwide 5G Infrastructure build out using Silicon Photonics fiber optic transceivers
- 3D and 2D Sensors including facial recognition in smartphones, tablets, and other applications
- Heterogeneous Integration of semiconductors and 3D fabrication and stacking driving technology and cost roadmaps pushing known good die with test and burn-in of device in wafer form prior to packaging











# FOX Family of Wafer Level Test & Burn-in Systems

#### **Solutions for Engineering to Production**



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Single Wafer Stepping Test & Burn-In System





Dual WaferPak & Dual DiePak Test & Burn-In System



FOX WaferPak Contactor



**FOX DiePak Carrier** 



Multi WaferPak & Multi DiePak Test & Burn-In Systems



### Aehr Wafer Level Test & Burn-in Patents





- WaferPak temperature control methods
  - Vacuum & pressure-based WaferPaks
    - Maintaining probe contact over temperature
      - Electrical components in WaferPak
        - Individual DUT power supplies
          - Per Die Current Protection
            - Redundant power supplies
              - Portable WaferPaks
                - And more . . .



## **Critical SiC MOSFET Parameters & Stress Tests**

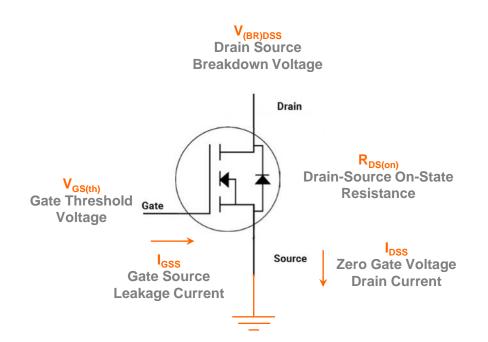
Higher than acceptable extrinsic (infant mortality) failure rates of silicon carbide MOSFETs require 100% production stress / burn-in testing to achieve automotive and industrial quality levels

#### **Example Stress / Burn-in Tests**

- Positive Gate Stress (HTGB+)
  - Positive Gate Voltage (Vgs)
- Negative Gate Stress (HTGB-)
  - Negative Gate Voltage (Vgs)
- Drain Stress (HTRB)
  - Positive Drain Voltage (Vds)

#### Body Diode Stress

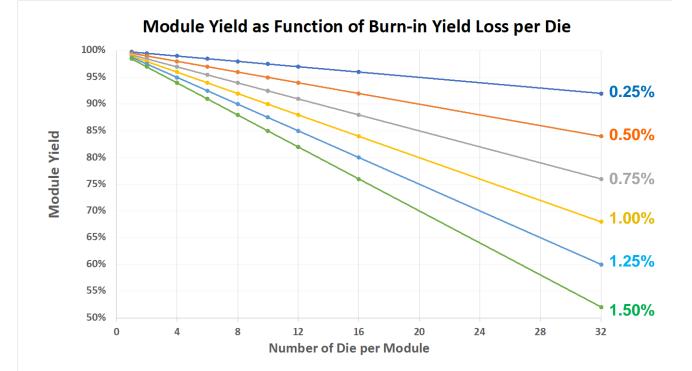
High Current Source from Source to Drain





### SiC and Multi-Die Packages / Modules





- Infant Mortality Yield loss of Modules linear with yield loss per die times number of die per module
- Cost of yield loss much greater than cost of burn-in test
- This is why the industry is driving to Wafer Level Burn-in



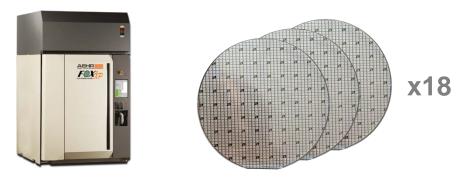
### Package Part vs Wafer Level Burn in

#### Package / Module Part Burn-in



- Up to ~ 2,500 SiC devices per system
- Individual device handling with limited life sockets and scrub marks on device leads
- Convection Thermal Control (Oven)
- Equipment depreciation cost of ~ \$0.01 per hour burn-in cost (fixed with standard discrete packages)

#### Wafer Level Burn-in



- Up to ~ 45,000 SiC devices per system
- 1000s of devices handled at a time with micro-pogo contact to die >> 100,000 cycle life
- Conduction Thermal Control (Thermal Chuck)
- Equipment depreciation cost of ~ \$0.01 per hour burnin cost (typical 500 die per wafer inverter MOSFET) and ~ \$0.002 per (2500 die per wafer charger or photovoltaic application MOSFET)



#### https://www.powerelectronicsnews.com/the-sic-mosfet-reliability-studies-at-the-ohio-state-university-threshold-voltage-stability-and-gate-oxide-screening-challenge

Ref: The SiC MOSFET Reliability Studies at the Ohio State University: Threshold Voltage Stability and Gate Oxide Screening Challenges

switch for a 400V rated battery

Vendor

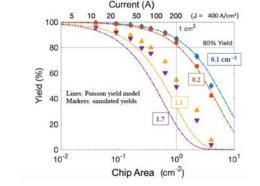
September 8, 2022 Sonu Daryanani

**SiC Modules** 

The largest SiC dies available at a 650V voltage rating are listed below

Rated Continuous ID at 25C (A)

Infineon	64	22	IMBG65R022M1H
ST Microelectronics	119	18	SCTWA90N65G2V-4
Wolfspeed	120	15	C3M0015065D

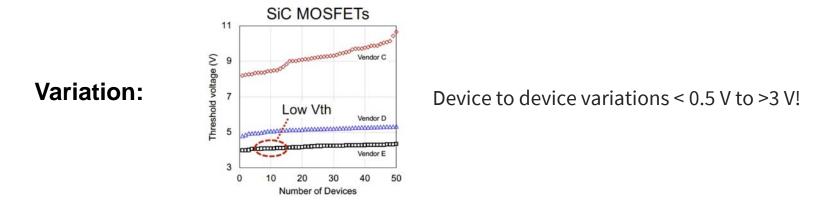


- Several devices needed in parallel for the 3-phase power module application.
- This can present challenges in matching device parameters within the module.
- The <u>variation</u> and drift of the threshold voltage in the SiC MOSFET is a major concern

Rdson Typ 25C (mOhms)

A 100kW 3-phase inverter for use in future Electric Vehicle (EV's) chargers needs a 450A to 550A rated

Part Number





# Variation of Devices' $V_{TH}$ in Modules

"With multiple devices in parallel that have different  $V_{TH}$ s, the device with the lowest  $V_{TH}$  will turn on first, and for a fraction of a second it will have a very large current passing through it until the others also turn on. This is momentary, but in an extreme case where there is a large difference this could be catastrophic, with the device being overloaded and failing. However, even in a more fractional case, the device with the lowest  $V_{TH}$  will be more highly stressed because it will take slightly more current in the switching phase, which could be detrimental to its long-term reliability compared to the rest."

Peter Gammon, Professor of Power Electronic Devices at University of Warwick

Module Manufacturers are requesting/requiring devices with matching V<sub>TH</sub> and/or R<sub>DSon</sub>



#### https://www.powerelectronicsnews.com/the-sic-mosfet-reliability-studies-at-the-ohio-state-university-threshold-voltage-stability-and-gate-oxide-screening-cha

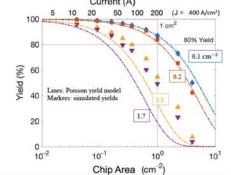
Ref: The SiC MOSFET Reliability Studies at the Ohio State University: Threshold Voltage Stability and Gate Oxide Screening Challenges

# SiC Modules

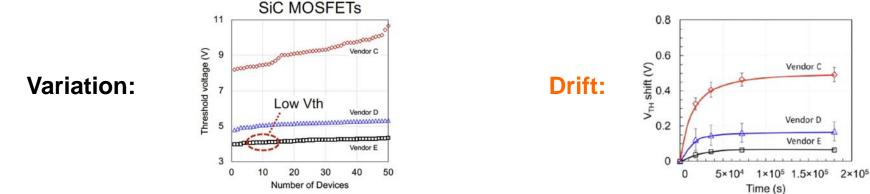
September 8, 2022 Sonu Daryanani

- A 100kW 3-phase inverter for use in future Electric Vehicle (EV's) chargers needs a 450A to 550A rated switch for a 400V rated battery Current (A)
- The largest SiC dies available at a 650V voltage rating are listed below

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## **V<sub>TH</sub> Stabilization during Stress / Burn-in Tests**

- Beyond Extrinsic (infant Mortality) Failure detection
- V<sub>TH</sub> substantially changes and stabilizes with time at elevated temperatures and elevated V<sub>GS</sub> levels
- Given the variation in the devices to begin with, do they stabilize in the same duration, to the same end or even relative  $V_{TH}$  levels?



## **FOX-NP SiC Gate and Drain Stress Test Solution**

#### FOX-NP Dual Wafer Test & Burn-In System



#### SiC MOSFET Gate Stress (HTGB)

- Programmable Gate voltage -30V to +40V
- Pulsing Gate Voltages
- Up to 150C

#### • SiC MOSFET Drain Stress (HTRB)

- Programmable Drain voltage up to 2,000V
- Up to 135C

#### • SiC MOSFET Body Diode Stress

- Programmable Source current up to > 1000A per wafer
- Up to 150C



FOX WaferPak Contactor



### **FOX-XP Production Test & Burn-In System**



FOX-XP 18 Wafer SiC Test & Burn-In System configured for SiC Gate Stress Test

#### 9 / 18 Wafer System for High Volume Production

- 100% compatible using the same Blade resources as FOX-NP
- Configurable for Gate, Drain, and Body Diode Stress tests
- Integrated standard 20°C to 150°C thermal control unit

#### FOX WaferPak Contactors

- Robust full wafer contactor with >> 100,000 cycle life
- High compliance / robust micro pogo pins
- Offline or online wafer alignment via Aehr proprietary WaferPak aligners



### **Aehr Fremont Applications Lab**



- FOX-XP Multi-Wafer WLBI System
- FOX-NP Dual-Wafer WLBI System
- FOX-CP Single Wafer Test Burn-in System with integrated high-power thermal chuck fully automated wafer prober
- FOX WaferPaks, DiePaks, & TLBs
- FOX WaferPak Automated Aligner
- FOX WaferPak Manual Aligner
- WaferPaks Racks & Accessories



# Aehr's SiC WLBI Qualification Program

- Customer and Aehr define success criteria for SiC wafer level qualification
- Aehr will develop and build a custom WaferPak and test program with monitoring for wafer level test and burn-in
- All development and testing can be done "remote and contact free" at Aehr Test Fremont facility
  - FOX-XP or NP Systems
  - Expert Test Engineering resources
  - Equipment and Devices in Aehr Fremont Clean Rooms
  - Remote access and video conferencing
  - 100% secure with restricted access, locks, and cameras

#### Aehr Fremont, CA Applications Lab





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